













ESD

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Product data sheet

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FMMT493 TRANSISTOR (NPN)



SOT -23



- 1 RASI
- 2. EMITTER
- 3. COLLECTOR

FEATURES

Complementary Type FMMT593

MARKING:493

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

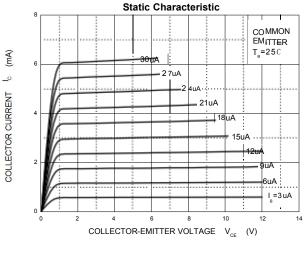
Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	120	V
Vceo	Collector-Emitter Voltage	100	V
V _{EBO}	Emitter-Base Voltage	5	V
lc	Collector Current	1000	mA
Pc	Collector Power Dissipation	250	mW
Roja	Thermal Resistance From Junction To Ambient	500	°C/W
Tj	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C

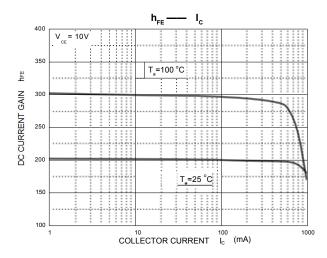
ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

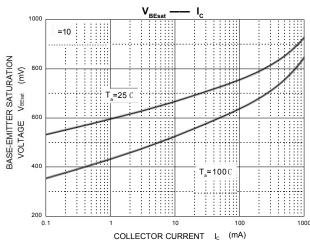
Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =100μA, I _E =0	120			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =10mA, I _B =0	100			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =100μA, I _C =0	5			V
Collector cut-off current	Ісво	V _{CB} =100V, I _E =0			0.1	μA
Collector cut-off current	Ices	V _{CES} =100V, I _E =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =4V, I _C =0			0.1	μΑ
	h _{FE(1)} *	V _{CE} =10V, I _C =1mA	100			
DC comment sein	h _{FE(2)} *	V _{CE} =10V, I _C =250mA	100		300	
DC current gain	h _{FE(3)} *	V _{CE} =10V, I _C =0.5A	60			
	h _{FE(4)} *	V _{CE} =10V, I _C =1A	20			
Collector-emitter saturation voltage	V _{CE(sat)1} *	Ic=500mA, I _B =50mA			0.3	V
Conector-entitler Saturation voltage	V _{CE(sat)2} *	I _C =1A, I _B =100mA			0.6	V
Base-emitter saturation voltage	V _{BE(sat)} *	I _C =1A, I _B =100mA			1.15	V
Base-emitter voltage	V _{BE} *	V _{CE} =10V, I _C =1A			1	V
Transition frequency	f _T	V _{CE} =10V,I _C =50mA, f=100MHz	150			MHz
Collector output capacitance	Cob	V _{CB} =10V, I _E =0, f=1MHz			10	pF

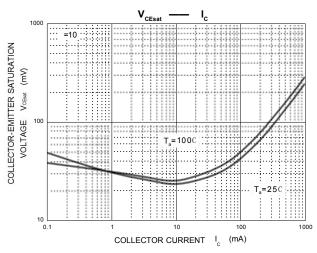
^{*}Pulse test: pulse width ≤300µs, duty cycle≤ 2.0%.

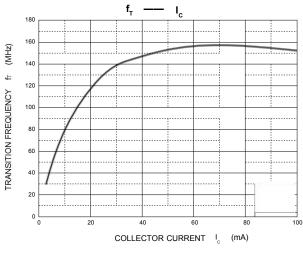


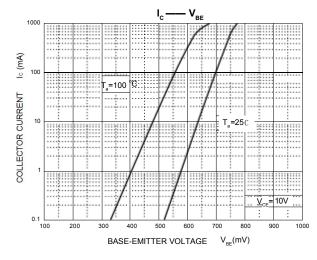


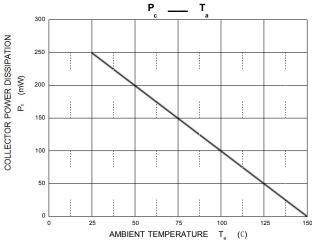




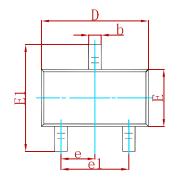


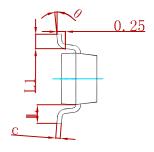


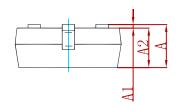




PACKAGE MECHANICAL DATA

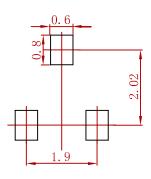






Combal	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.03	7 TYP	
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

Suggested Pad Layout



Note:

- 1.Controlling dimension:in millimeters.
- General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
FMMT493	SOT-23	3000



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